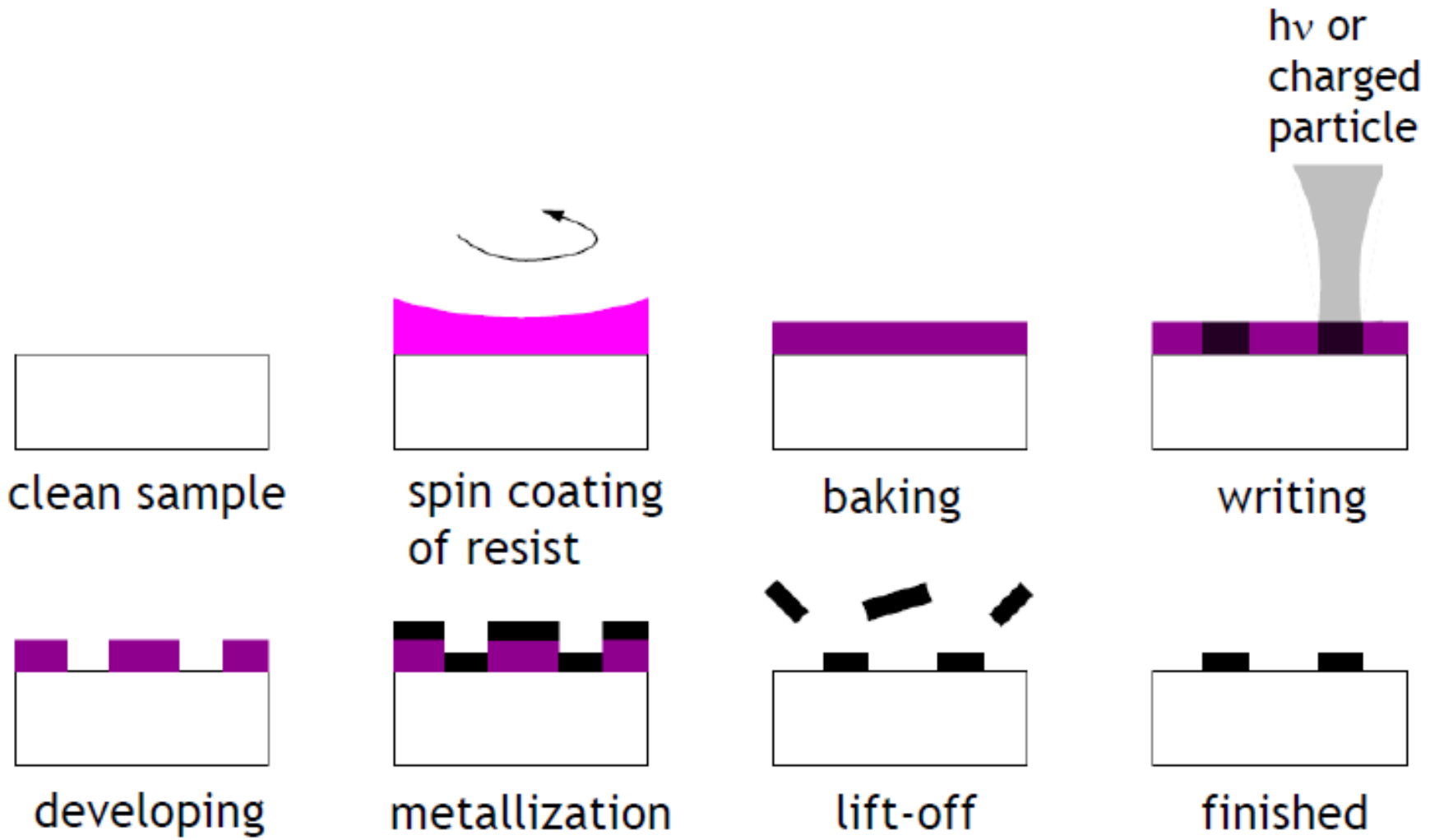
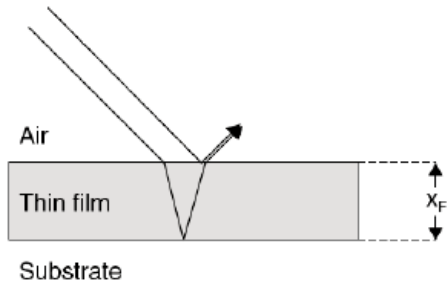


- Litography: photo, e-beam
- Focused Ion Beam (FIB)
- Nano imprinting

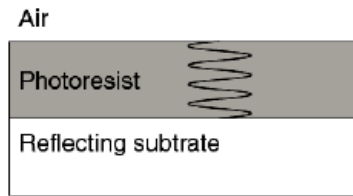
- Molecular beam epitaxy (MBE)
- Self assembly
- Chemical vapor deposition (CVD)
- Atomic manipulation (STM)



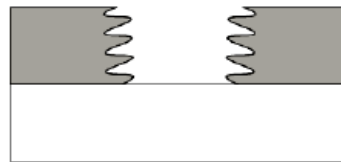
Interference



reflection from film/air and film/substrate interface can produce variation of light intensity due to a standing wave:



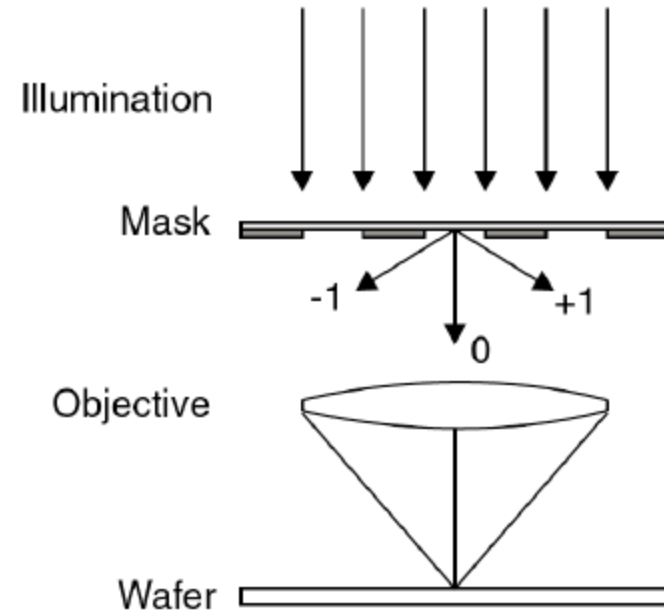
Standing wave



Resulting profile

Diffraction limit

coherent illumination

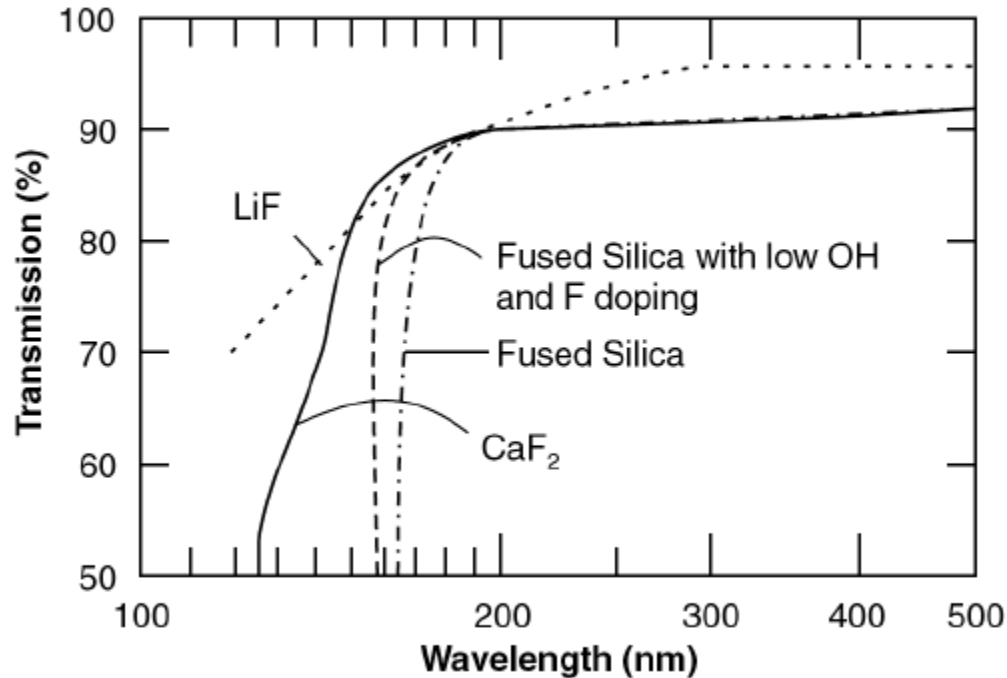


1st order diffraction: $\sin \Theta = \frac{\lambda}{d} = NA$

minimum resolvable line width: $W = 0.5d = \boxed{0.5} \frac{\lambda}{NA}$

NA = numerical aperture ~ 1.5 in modern optics

issue: optical transparency of available lens materials



below 200 nm, only special low-doped fused silica and CaF₂ are suitable

Limit ~100 nm

Electrons in place of photons

$$\lambda = h / (2 m e V)^{1/2}$$



No diffraction limit, but ...

$$e \text{ energy} = 200 \text{ eV} \rightarrow \lambda \sim 0.09 \text{ nm}$$

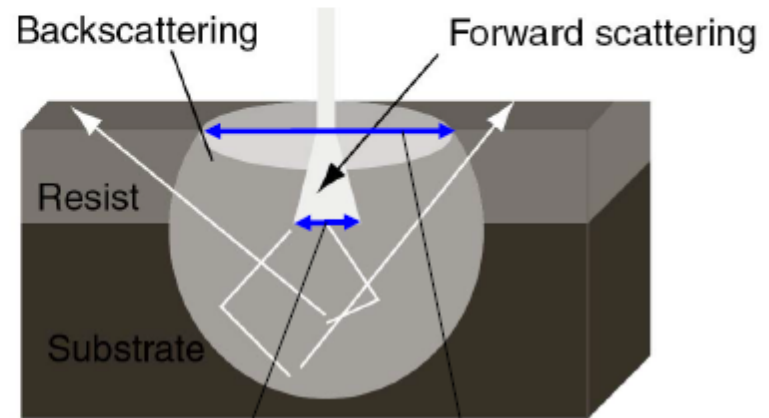
two-Gaussian model (Monte Carlo simulation):

characteristic diameter for forward-traveling electrons

$$\sigma_f [\mu\text{m}] = \left(\frac{9.6 z [\mu\text{m}]}{V [\text{keV}]} \right)$$

z ... thickness of resist film
V ... energy of incident e-beam

for $V = 20 \text{ keV}$ and $z = 500 \text{ nm}$
 $\rightarrow \sigma_f = 80 \text{ nm}$



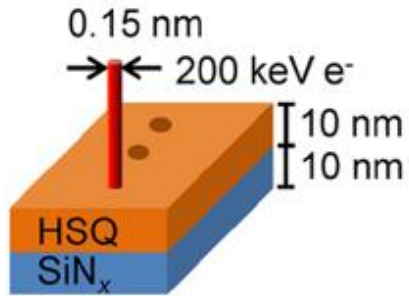
...for backward-traveling electrons

$$\sigma_b = \text{several } \mu\text{m}$$

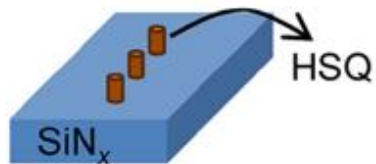
limits resolution

2 nm isolated feature size and 5 nm half-pitch

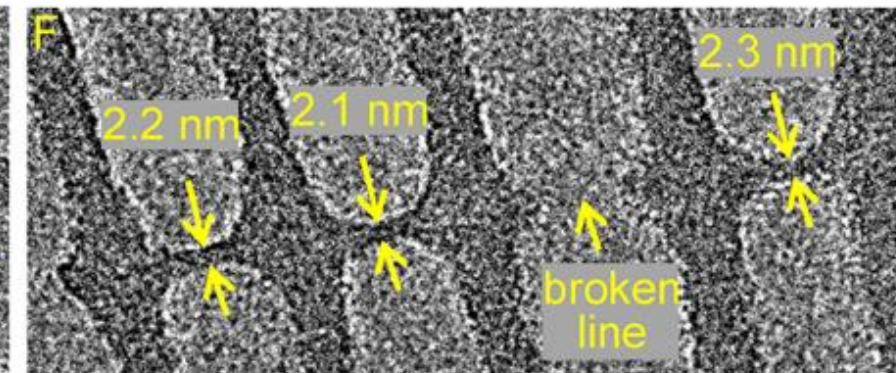
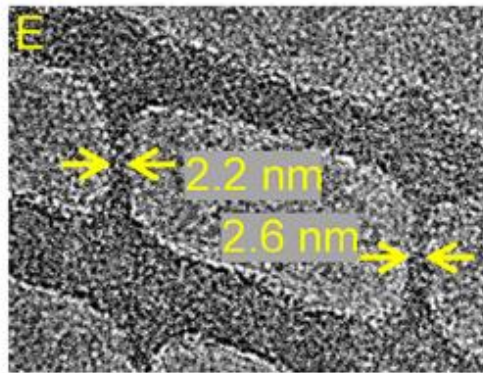
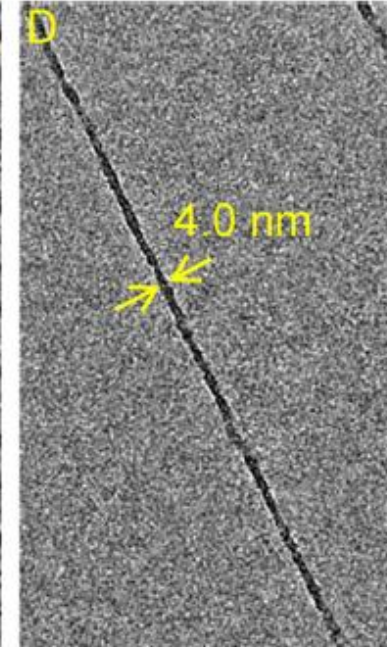
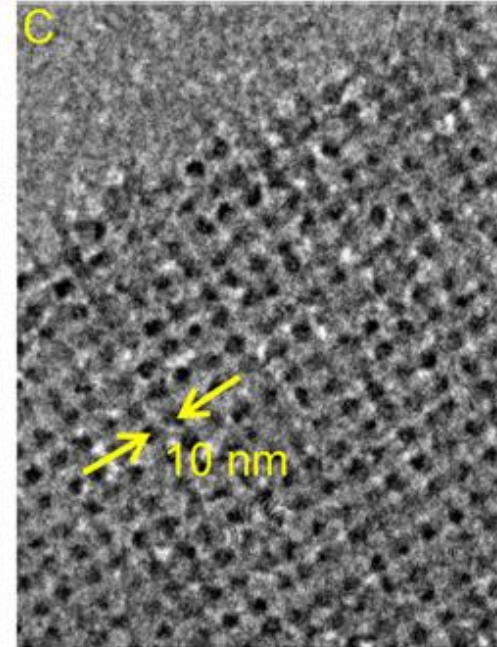
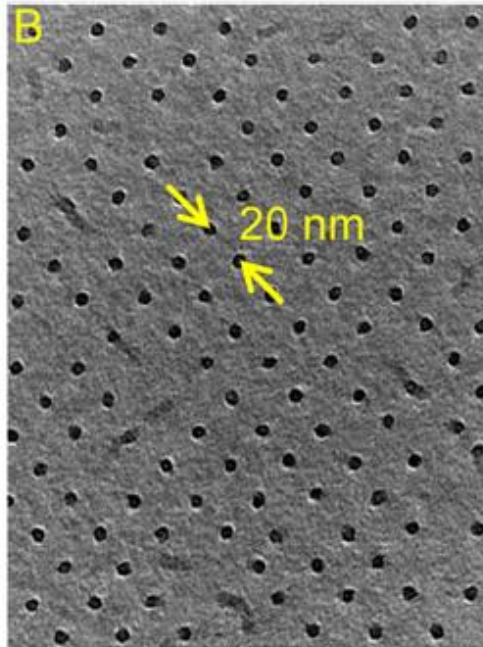
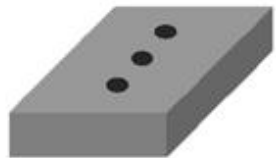
A
(1) aberration-corrected
STEM exposure



(2) development



(3) TEM metrology



STEM = **Scanning** Transmission Electron Microscope -> serial process
-> long process for nm patterns repeated on in² surfaces



Deposition Rate F



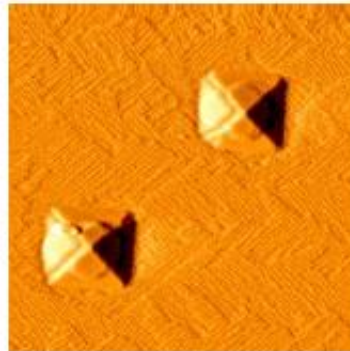
Diffusion D

Arrhenius Law (Temp. T)

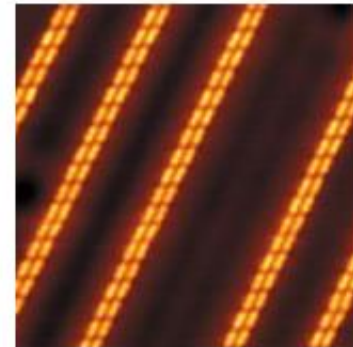
$$D \sim n_0 \exp(-E_{\text{barrier}}/k_B T)$$



metal epitaxy



semiconductor
MBE



molecular
self-assembly

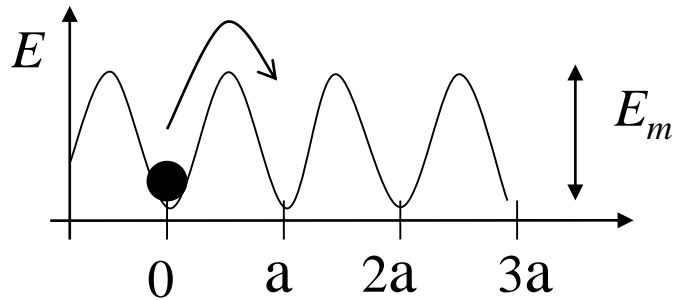
Epitaxial thin film growth is a non-equilibrium kinetic phenomena.

In thermodynamic equilibrium all atomic processes proceed in opposite directions at equal rates, i.e. there is hence no net growth and average macroscopic quantities such as surface coverage or roughness stay constant.

a 2D laboratory: single crystal surfaces

each process i has
an energy barrier E_i and a rate v

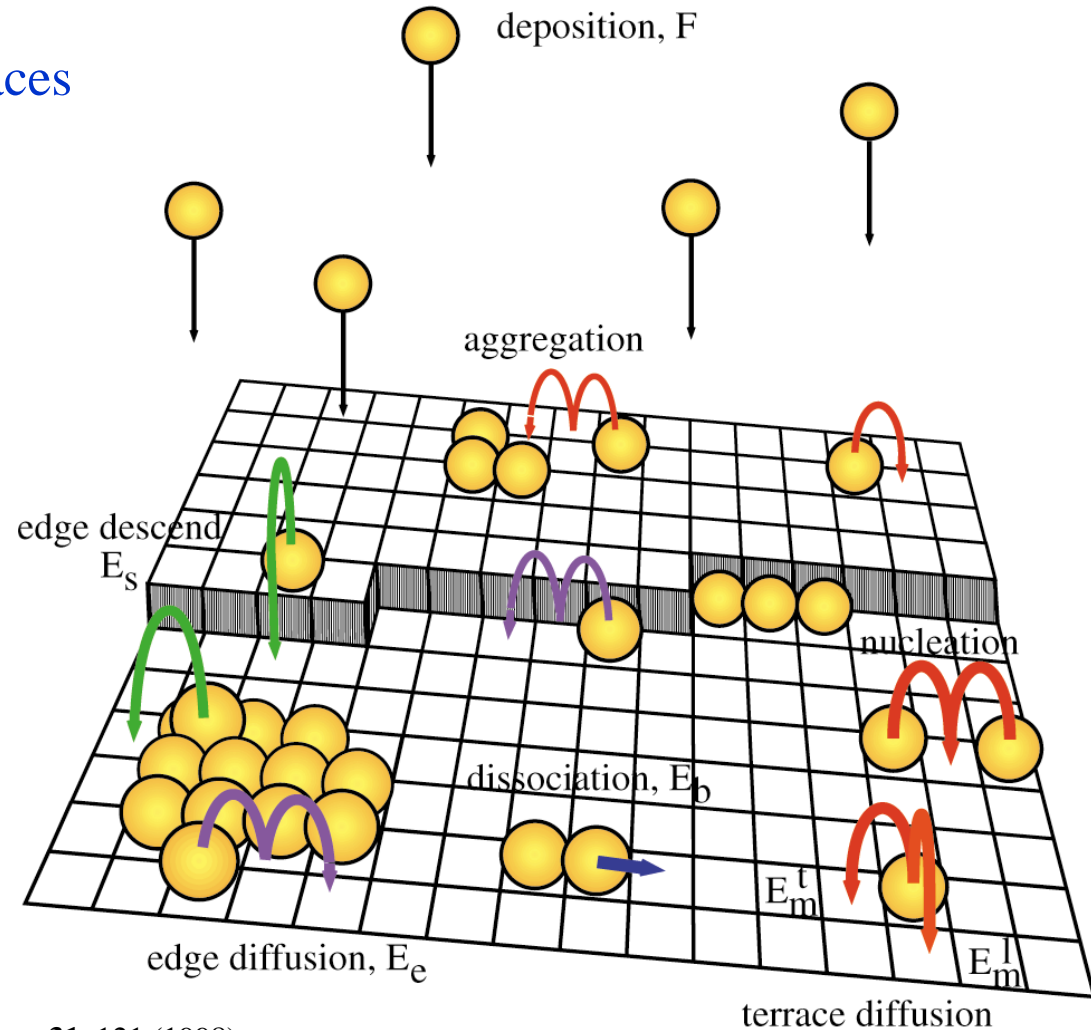
$$v = v_0 \exp(-E_i / kT)$$



diffusion processes:

$$\langle \Delta r^2 \rangle = v a^2 t$$

$a \rightarrow$ lattice constant, $t \rightarrow$ time



Aim: controlling

- mean size
(size distribution)
- density
- shape
- composition

Control parameters:

- substrate temperature T
- deposition flux F
- surface coverage Θ
- substrate/overlayer material
(strain, mixing, etc.)
- substrate symmetry or
patterning

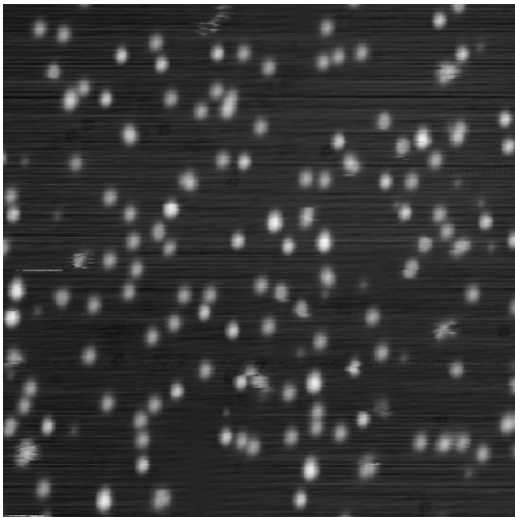
- thermally-activated diffusion is frozen

$$\nu = \nu_0 \exp(-E_i / kT) \rightarrow 0$$

- coverage determines mean island size n
- large size distribution

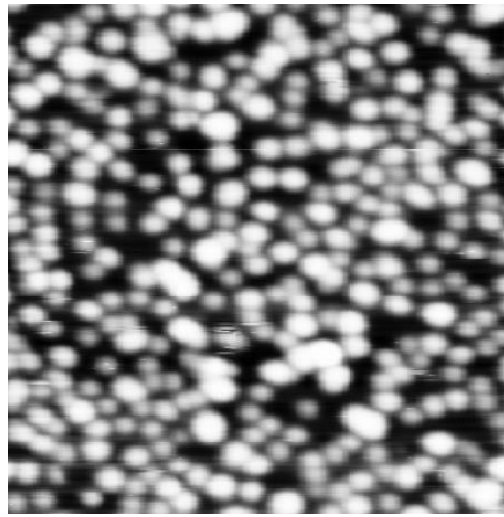
Co/Pt(111)

0.03 ML, $T = 50$ K:
 $n = 1.2$



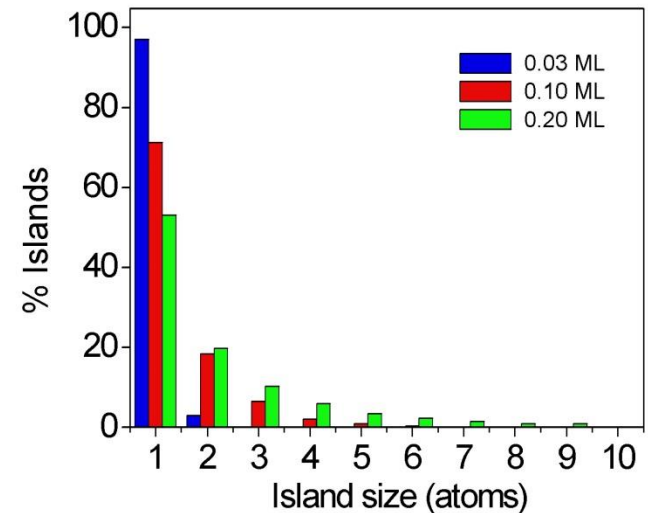
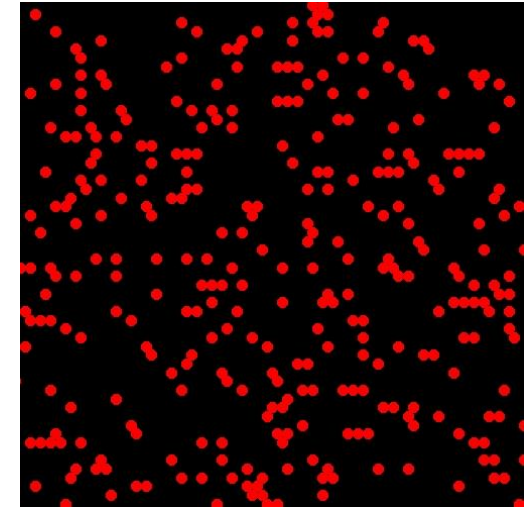
50 Å

0.10 ML, $T = 50$ K:
 $n = 2.9$

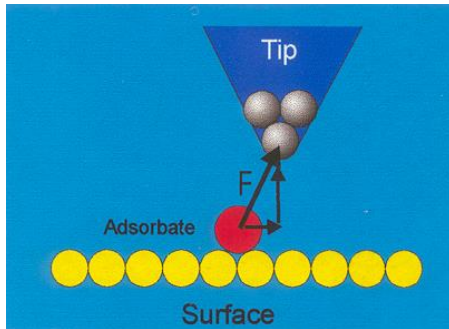


50 Å

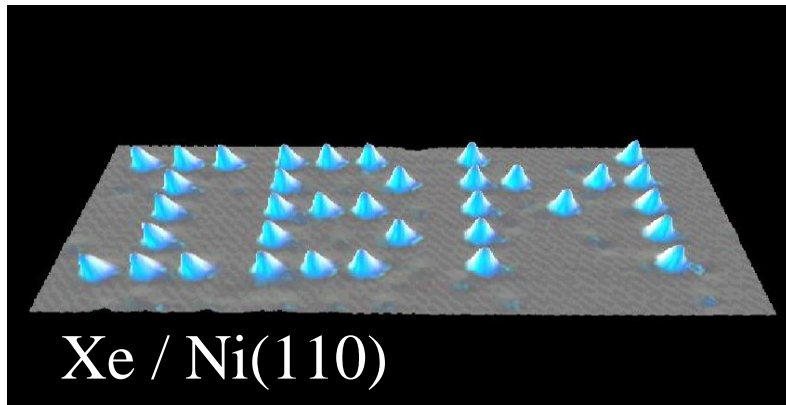
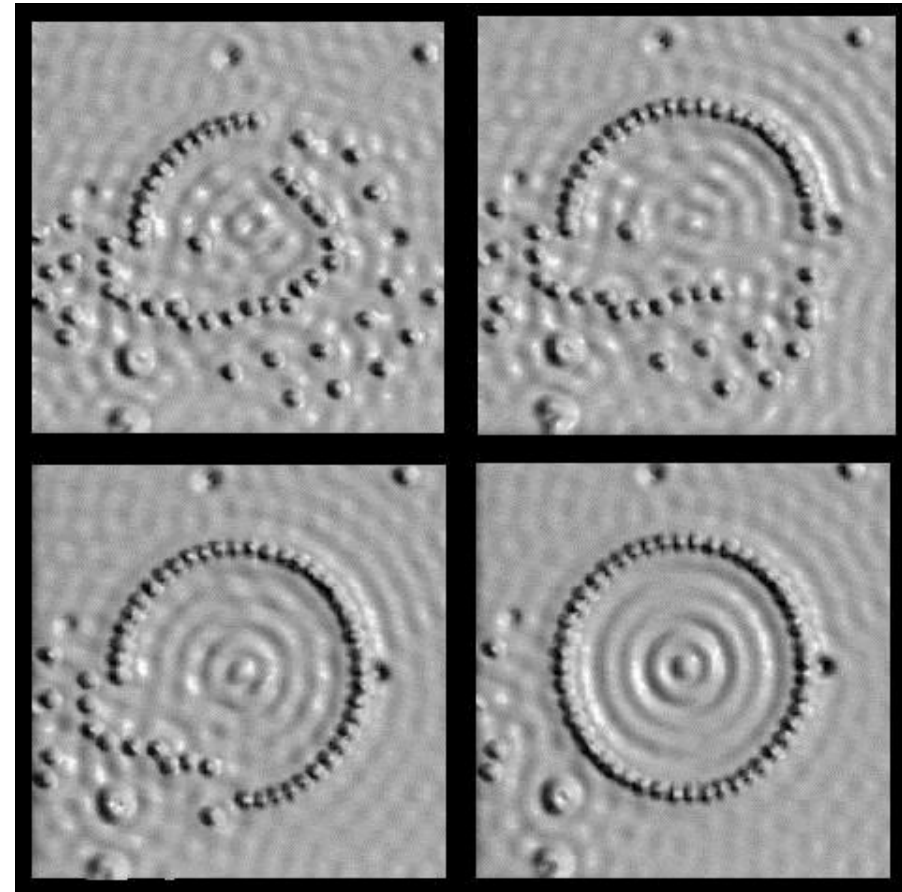
Kinetic Monte Carlo simulation



$n = \text{mean island size} = \text{coverage/island density}$



Quantum corral



D. Eigler & E. Schweizer,
Nature **344**, 524 (1990)

Fe on Cu(111)

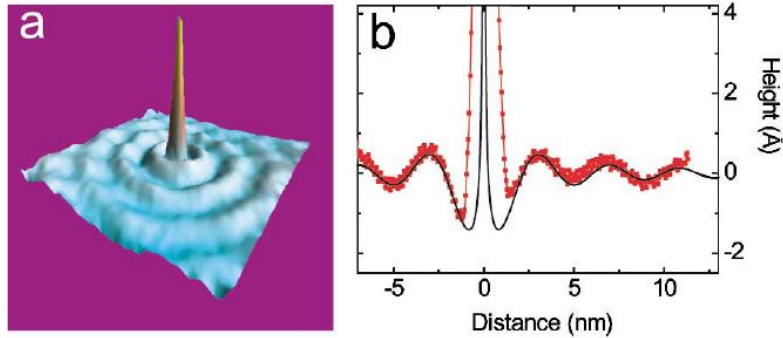
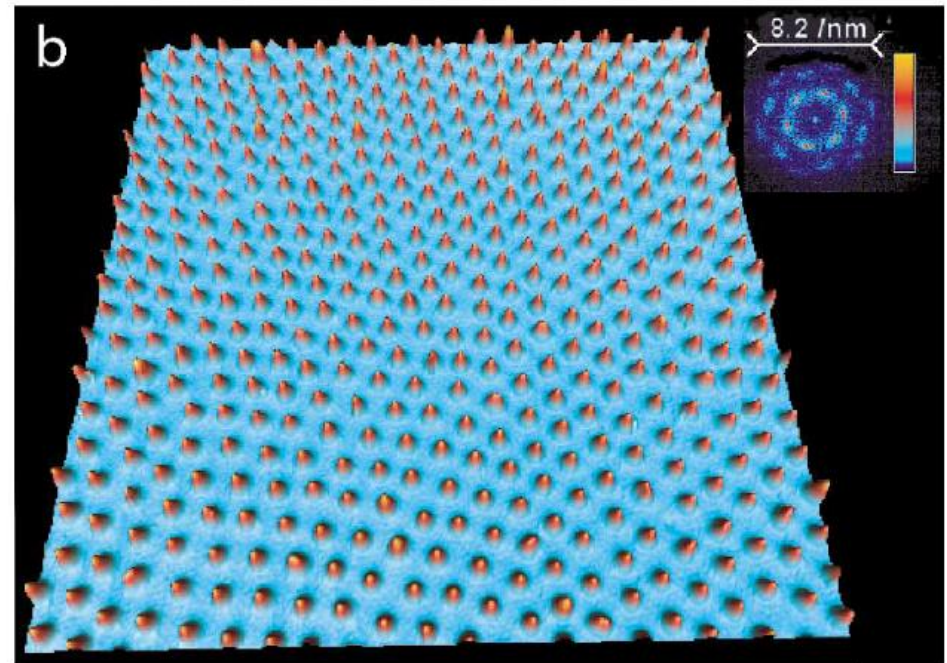
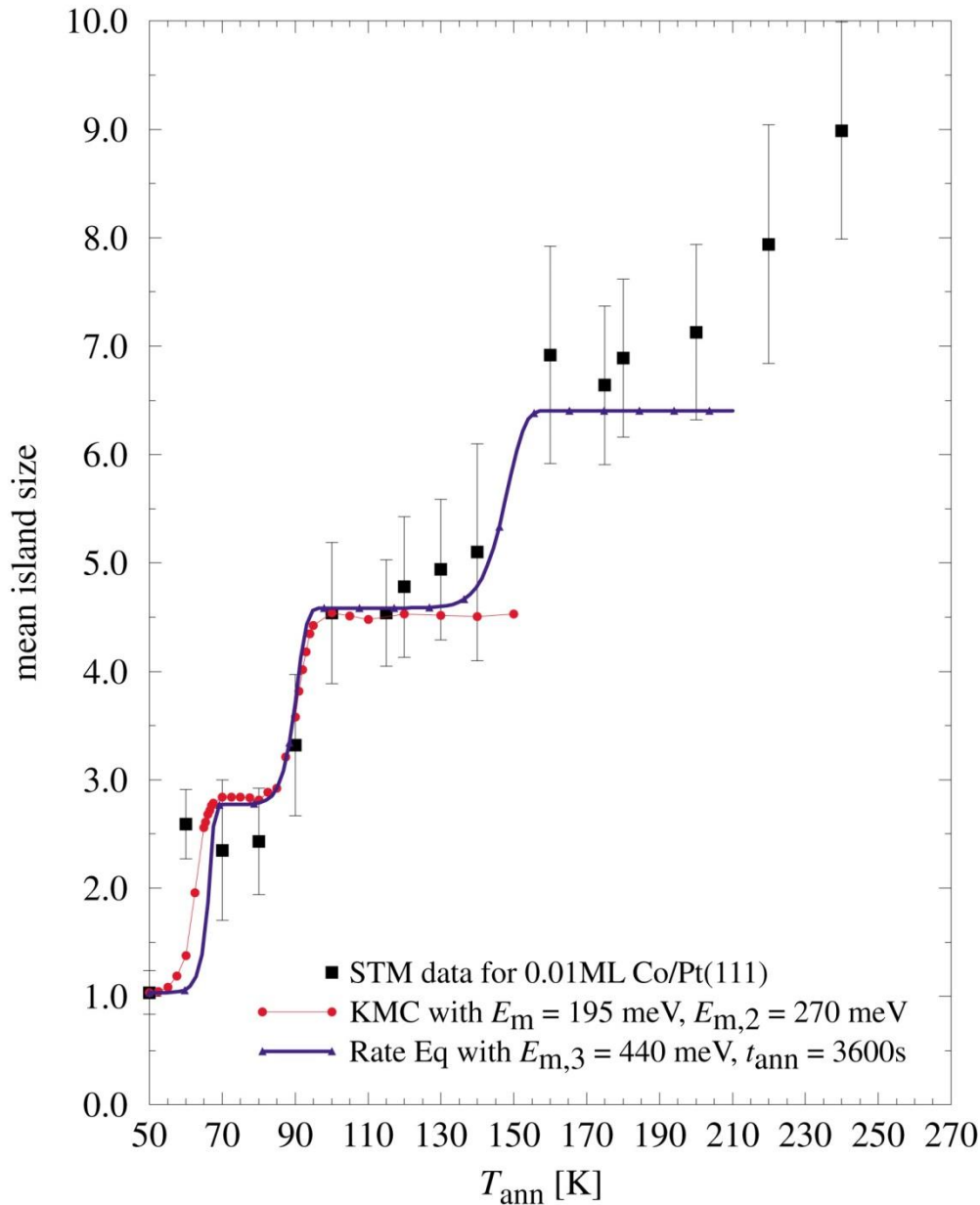


FIG. 3 (color online). (a) The $21 \times 21 \text{ nm}^2$ 3D STM image of a standing-wave pattern around an isolated Ce adatom on Ag(111) at 3.9 K ($U_s = -3 \text{ mV}$, $I_s = 19 \text{ pA}$). (b) Dotted line: topographic profile as a function of distance from a single Ce adatom. Solid line: fit using Eq. (1).

At the Fermi energy (E_F) the local density of states (LDOS) oscillates around the impurity with a wavelength of $\lambda_F = 2\pi/k_F$, where λ_F is the Fermi wavelength and k_F the Fermi wave vector. This variation of the LDOS at E_F due to standing-wave formation modifies the adsorption energy of the adsorbates.

Ce superlattice on Ag(111) at 4.8 K



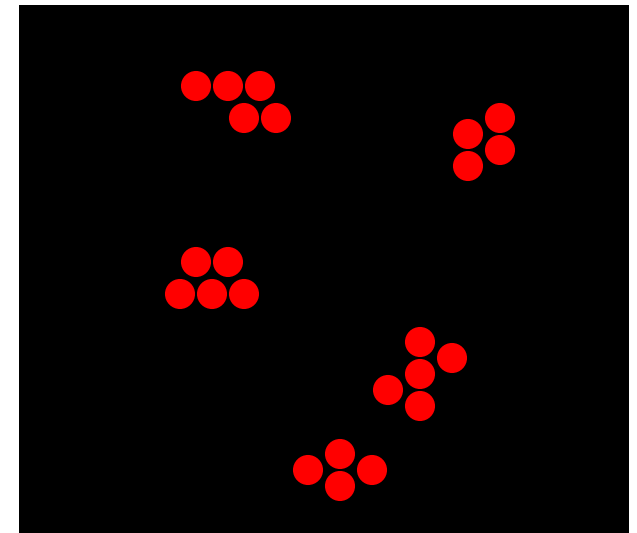


Sequential activation of cluster diffusion results in size selection

$T < 60$ K: monomers

$60 \text{ K} < T < 90 \text{ K}$: dimers and trimers

$100 \text{ K} < T < 130 \text{ K}$: tetramers and pentamers



Assumption: adatom can diffuse with a rate D
but

dimer is stable, i.e. when two atoms meet, they can not detach
Critical size (nucleus) $i=1$

Dimer creation

Adatom density

Growth flux

Adatom-island attachment

$$\frac{dn_1}{dt} = F - 2\sigma_1 D n_1^2 - \sigma_x D n_1 n_x - k_x F (Ft - n_1) - 2k_1 F n_1$$

$$\frac{dn_x}{dt} = \sigma_1 D n_1^2 + k_1 F n_1$$

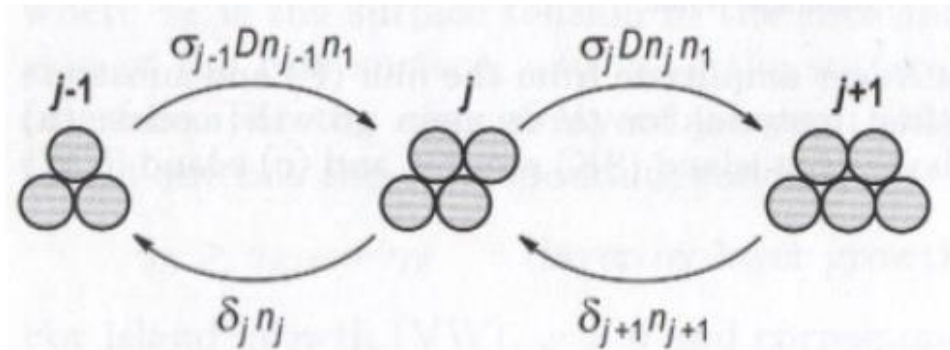
$$D = D_0 \exp(-E_m / kT)$$

Direct impinging on an island

Direct impinging on an adatom

Rate equations give the formation rate for adatom and stable islands

- Capture and decay processes \rightarrow cluster size



- Rate equations:

$$\frac{dn_1}{dt} = \underbrace{R}_{\text{deposition rate}} - \frac{n_1}{\tau_{ads}} + \underbrace{\left(2\delta_2 n_2 + \sum_{j=3}^i \delta_j n_j - 2\sigma_1 D n_1^2 - n_1 \sum_{j=2}^i \sigma_j D n_j \right)}_{\text{subcritical clusters}} - \underbrace{n_1 \sigma_x D n_x}_{\text{stable clusters}}$$

↑ adatom density
↓ deposition rate

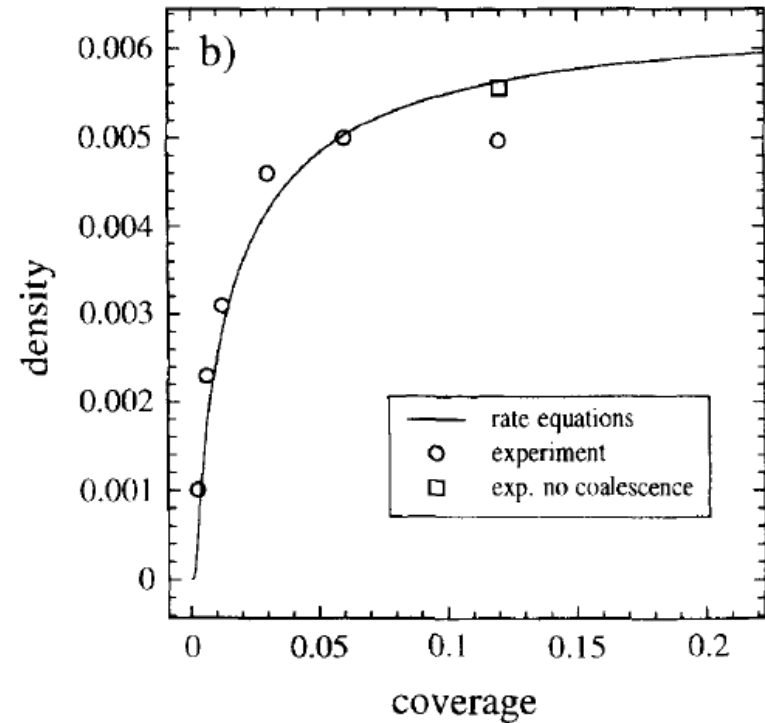
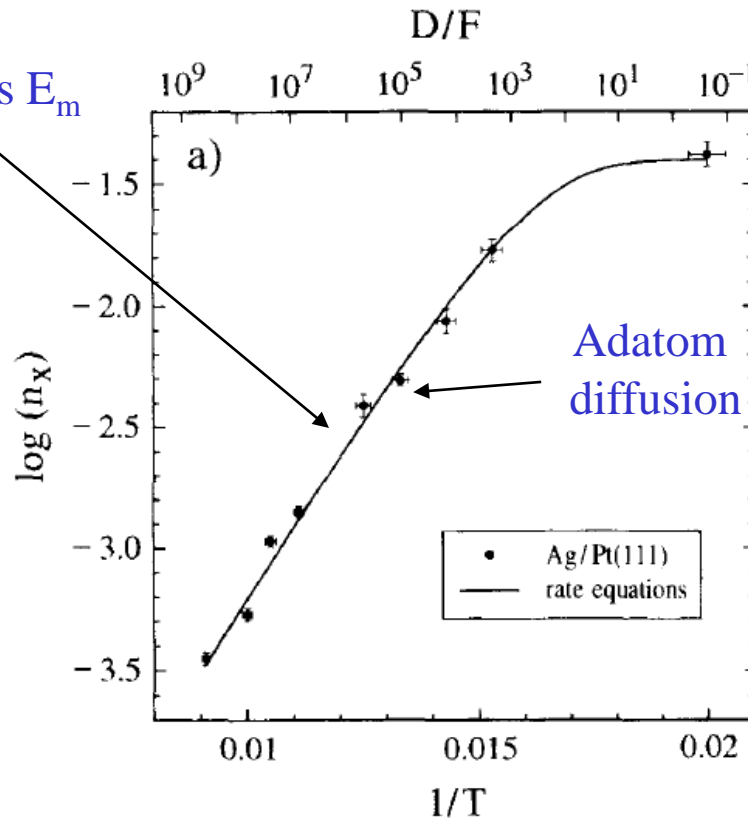
$$\frac{dn_j}{dt} = n_1 \sigma_{j-1} D n_{j-1} - \delta_j n_j + \delta_{j+1} n_{j+1} - n_1 \sigma_j D n_j \longrightarrow \text{metastable clusters}$$

$$\frac{dn_x}{dt} = n_1 \sigma_i D n_i \longrightarrow \text{stable clusters}$$

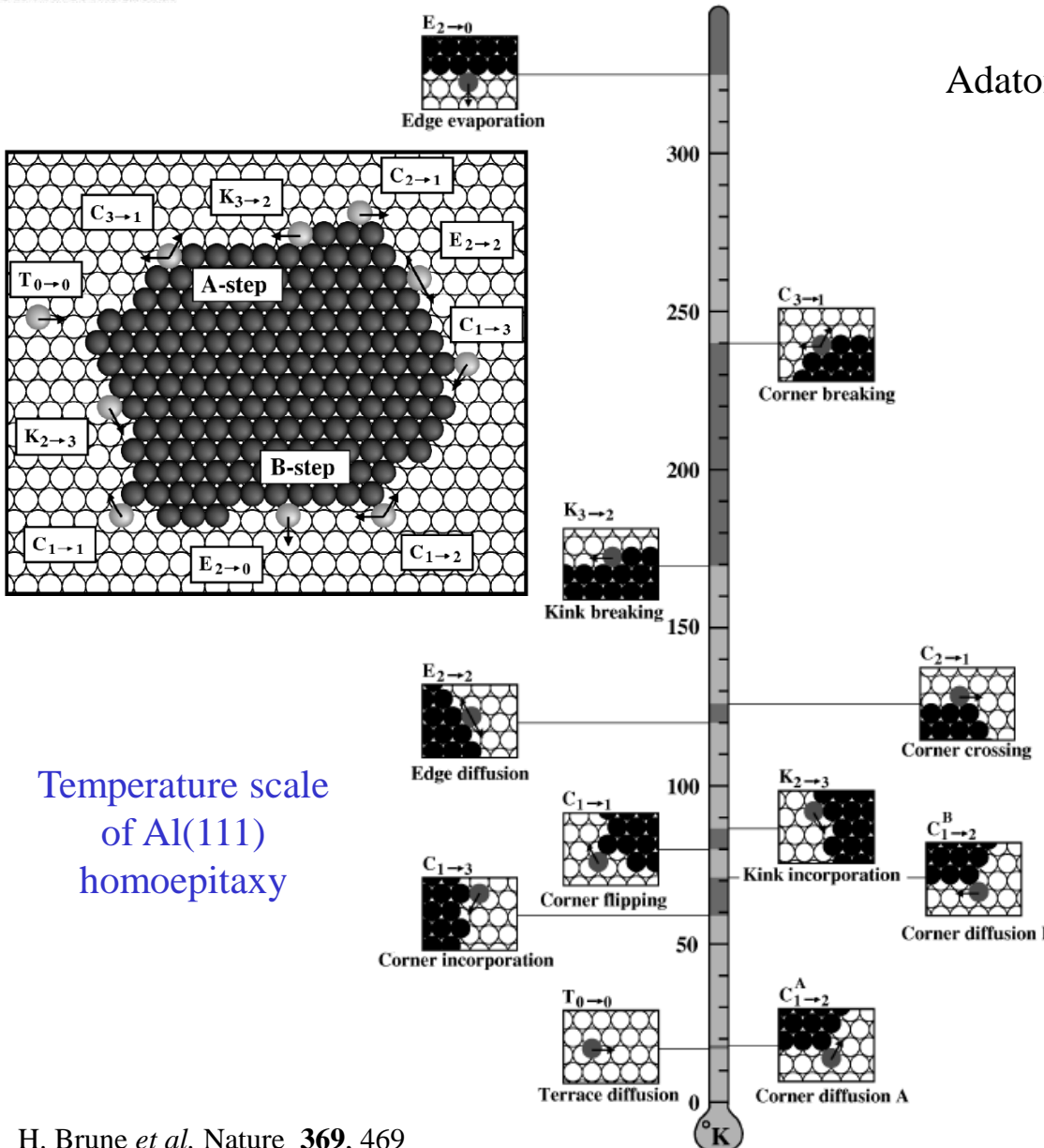
$$n_x = \eta(\theta, i) \left(\frac{D}{F} \right)^{-\chi} \exp\left(\frac{E_i}{(i+2)kT} \right) \quad \chi = \frac{i}{i+2}$$

$$i=1 \rightarrow E_i = 0 \rightarrow n_x = \eta(\theta, i) \left(\frac{D}{F} \right)^{-1/3} = n_x = \eta(\theta, i) \left(\frac{D_0}{F} \right)^{-1/3} \exp\left(\frac{E_m}{3kT} \right)$$

The slope gives E_m



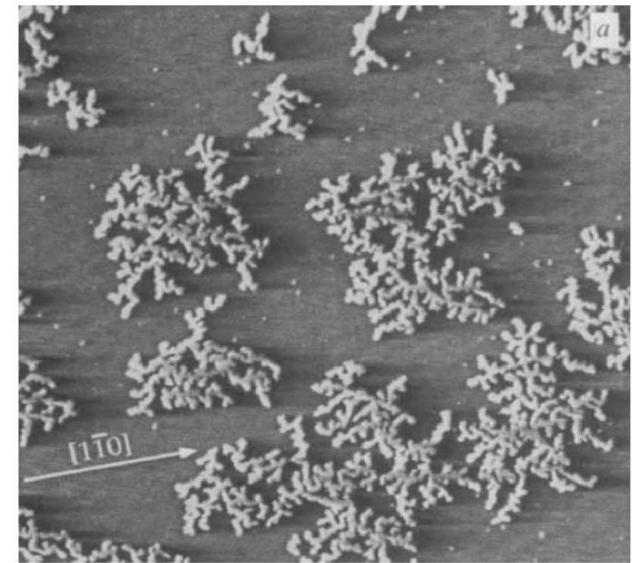
Comparison of experimental island densities for Ag/Pt(111) with self-consistent calculations from mean-field nucleation theory. (a) Arrhenius plot of saturation island densities ((cov. = 0.12 ML) for the regime where dimers are stable nuclei. (b) Island density vs. coverage at 75 K).



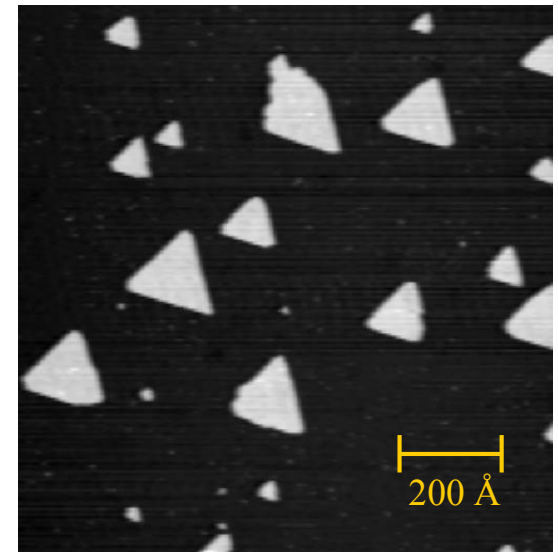
Temperature scale
of Al(111)
homoepitaxy

Ag/Pt(111) T=110K:

Adatom stick at the island edge and stop diffusing



20 nm

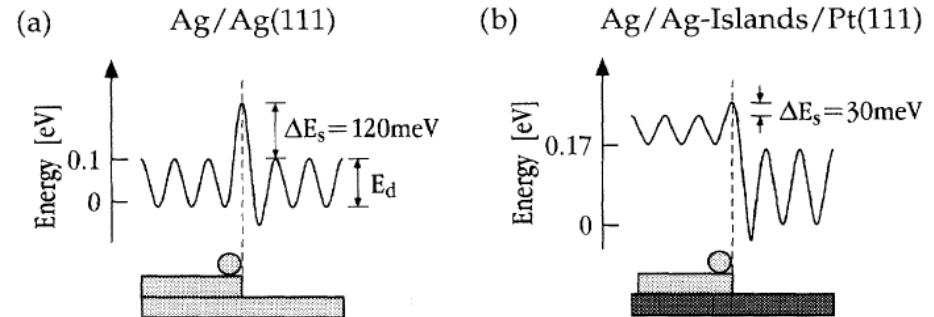
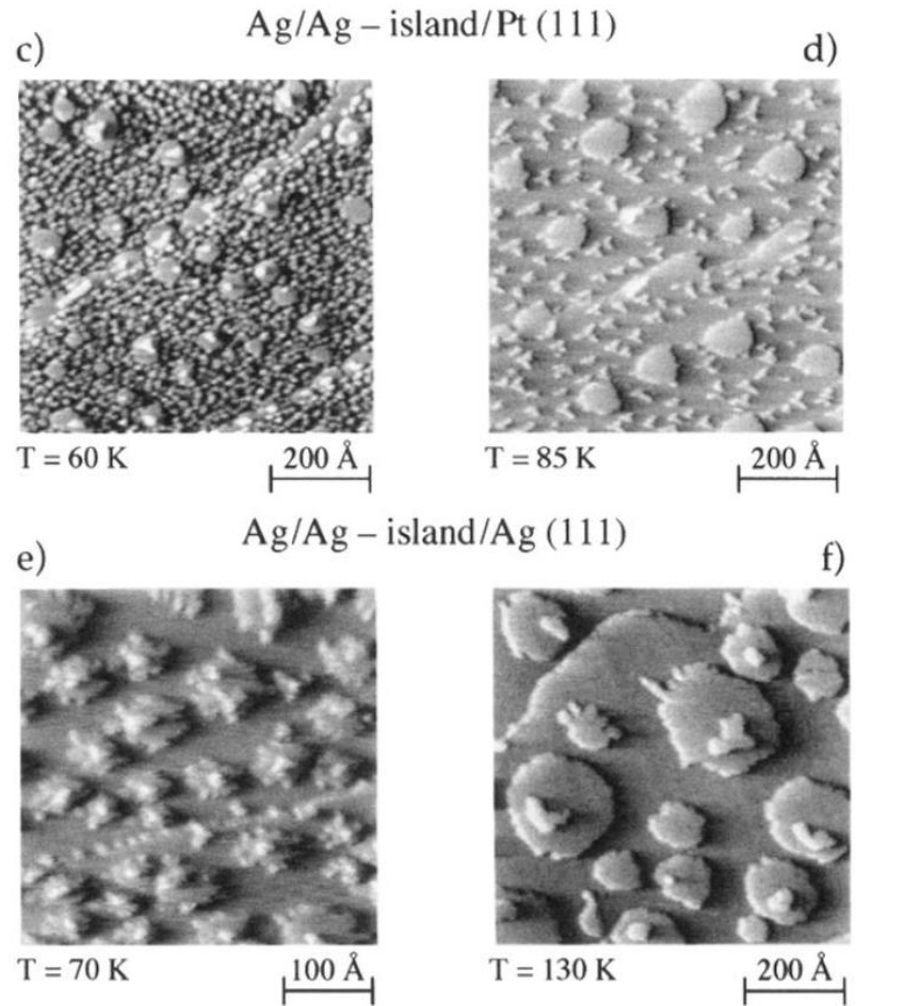
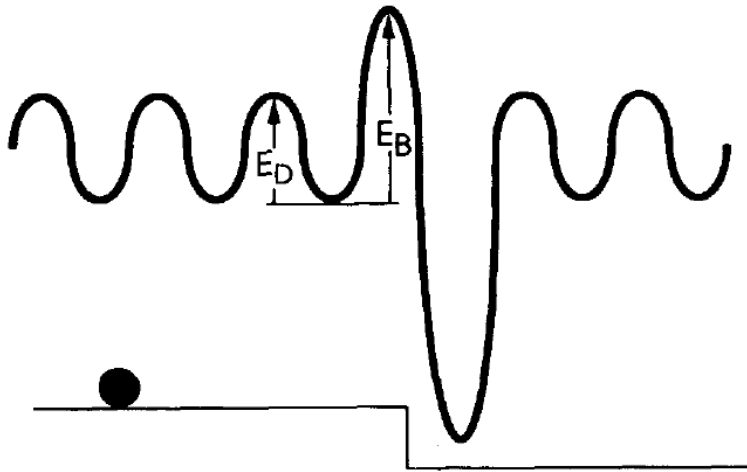


Co/Pt(111) T=270K:

Adatom edge diffusion is activated

H. Brune *et al.* Nature **369**, 469 (1994); S. Ovesson *et al.* Phys. Rev. Lett. **83**, 2608 (1999); A. Bogicevic *et al.* **81**, 637 (1998)

Schematic of the energy landscape seen by an adatom approaching a step edge



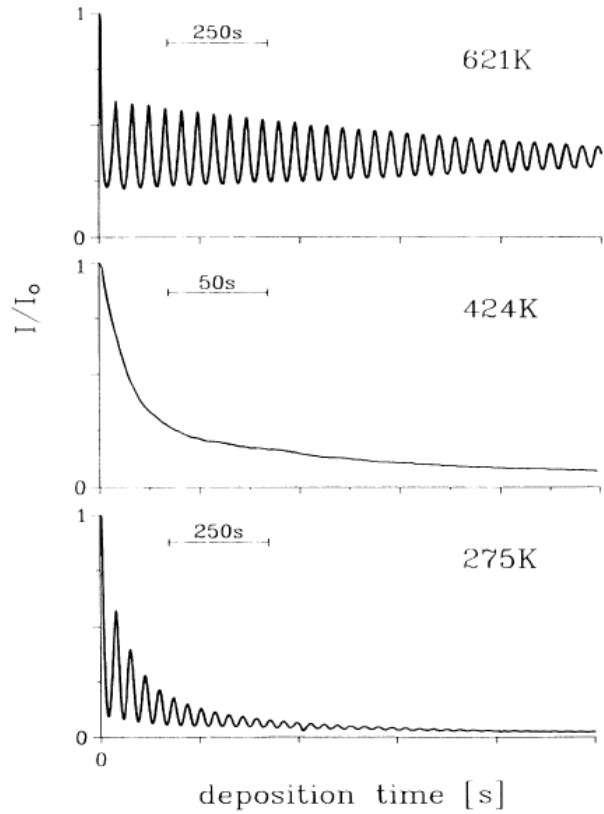


FIG. 1. The normalized He specular peak height vs Pt on Pt(111) deposition time measured at three different surface temperatures. All other parameters including the deposition rate (confined between 1/40.6 and 1/36 ML/s) are identical. The oscillatory behavior at high and low temperature is evidence for layer-by-layer growth (denoted in the text by $2D_h$ and $2D_l$ growth, respectively); the monotonic decrease in the intermediate region indicates 3D growth.

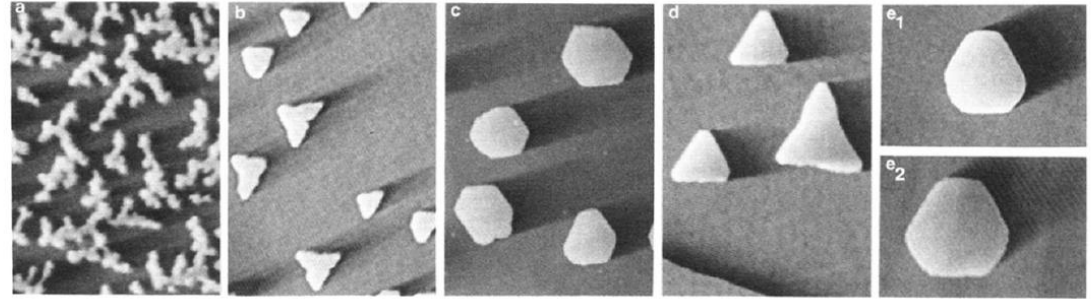
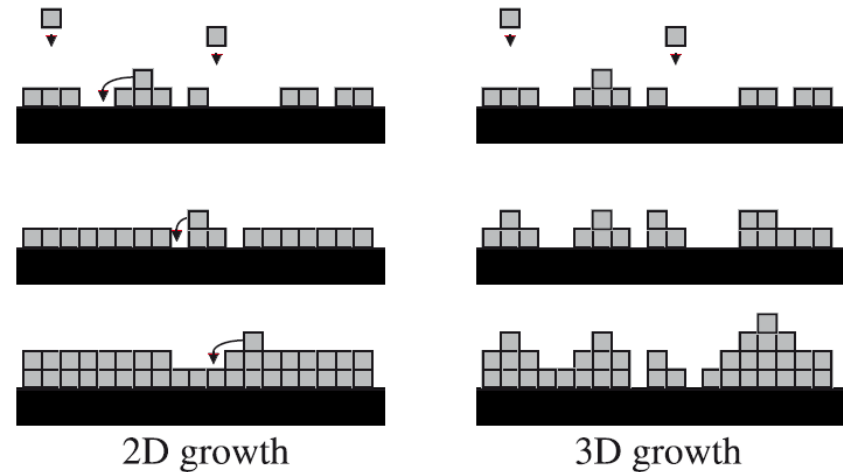


FIG. 1. Island shapes on Pt(111) resulting at various surface temperatures T_s after deposition of an amount Θ with a typical rate of 1×10^{-2} ML/s on images with a size S . (a) $T_s = 200$ K, $\Theta = 0.2$ ML, $S = 280 \text{ \AA} \times 400 \text{ \AA}$; (b) $T_s = 400$ K, $\Theta = 0.08$ ML, $S = 1300 \text{ \AA} \times 1900 \text{ \AA}$; (c) $T_s = 455$ K, $\Theta = 0.14$ ML, $S = 770 \text{ \AA} \times 1100 \text{ \AA}$; (d) $T_s = 640$ K, $\Theta = 0.15$ ML, $S = 2300 \text{ \AA} \times 3300 \text{ \AA}$; (e₁) $T_s = 710$ K, $\Theta = 0.08$ ML, $S = 1540 \text{ \AA} \times 1100 \text{ \AA}$; (e₂) after deposition at $T_s = 425$ K ($\Theta = 0.08$ ML) the sample was additionally annealed to 710 K for 1 min and then imaged ($S = 630 \text{ \AA} \times 900 \text{ \AA}$).



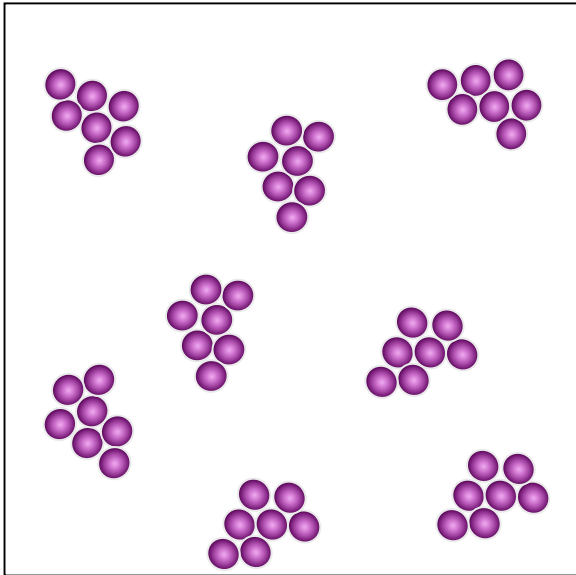
Inter-layer diffusion depends on the island size and shape

Fe

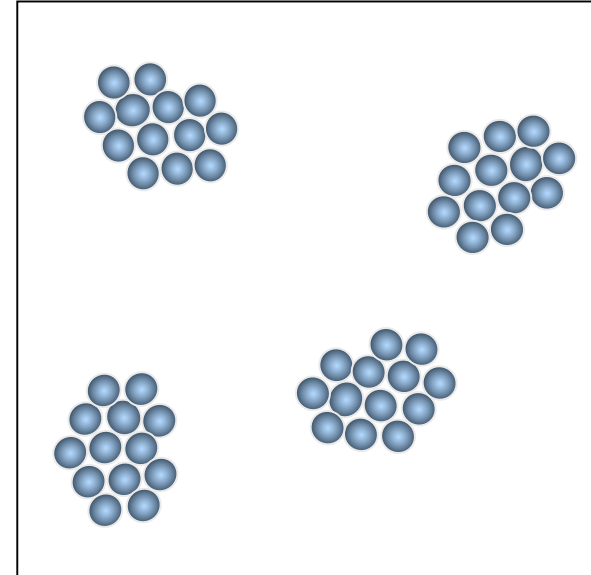
Co



$$v = v_0 \exp(-E_i / kT)$$



$$v = v_0 \exp(-E_i / kT)$$



Fe

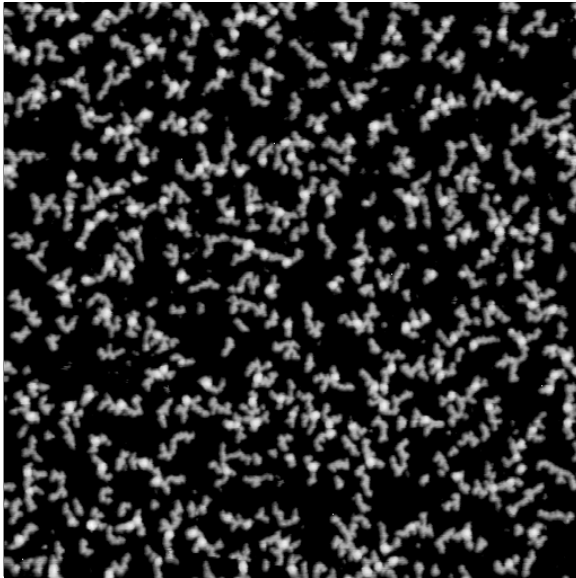
Co



$$v = v_0 \exp(-E_i / kT)$$



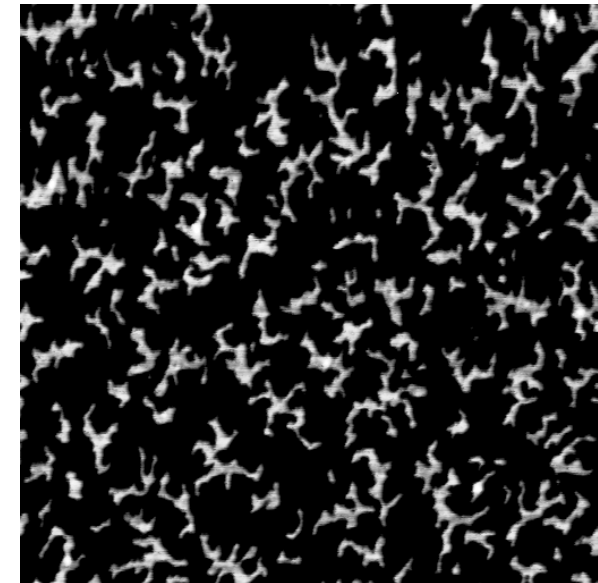
$$v = v_0 \exp(-E_i / kT)$$



27 nm

Island size = 90 atoms/isl

$T_{\text{dep}} = 140 \text{ K}$
 $\Theta = 0.25 \text{ ML}$



30 nm

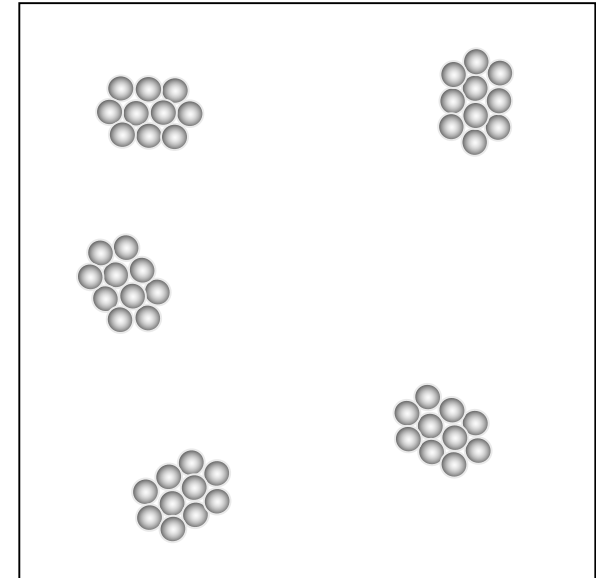
Island size = 390 atoms/isl

Alloy ($\text{Fe}_x\text{Co}_{1-x}$) growth by co-deposition:
the island size (density) depends on the relative percentage of the two elements!!!!

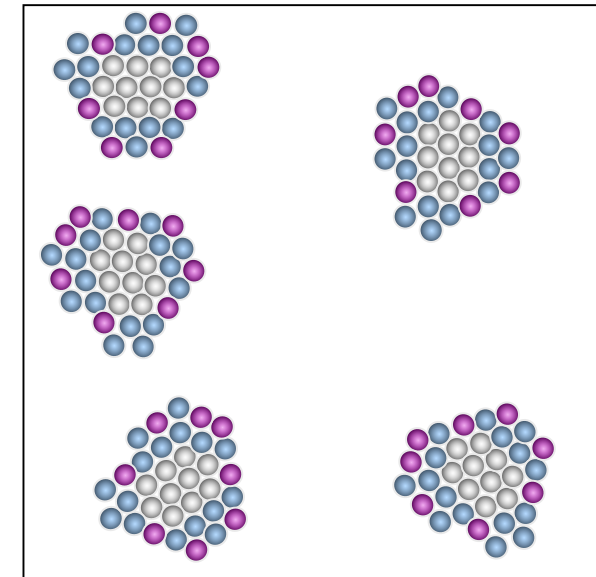


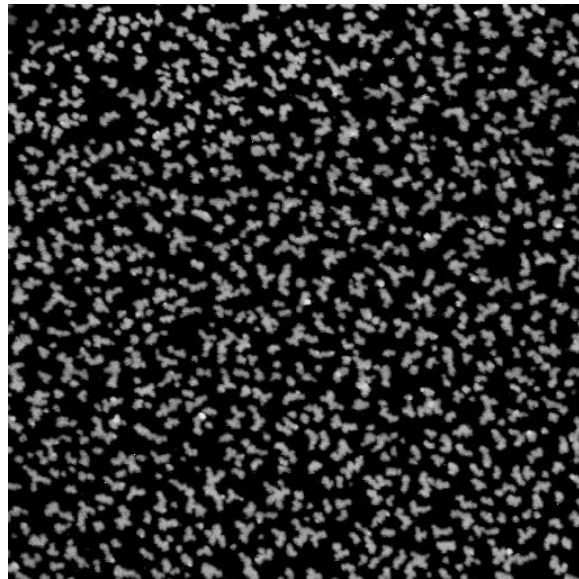
Nanostructured surface

Pre-defined nucleation sites to
define the island density



Growth of the alloyed nanostructures
on the template substrate



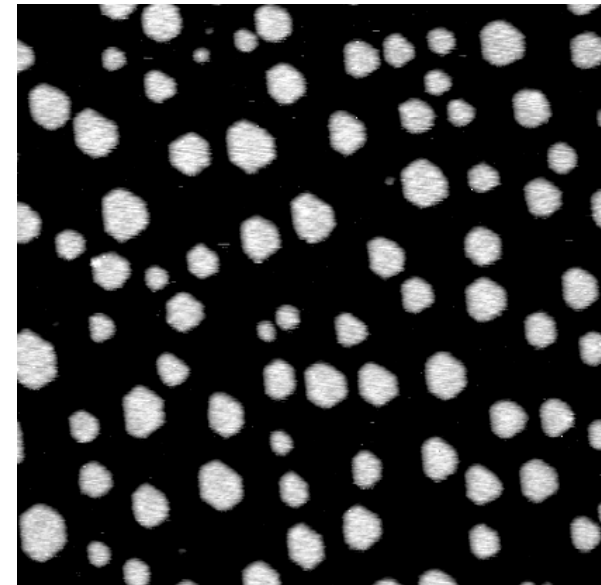


10 nm

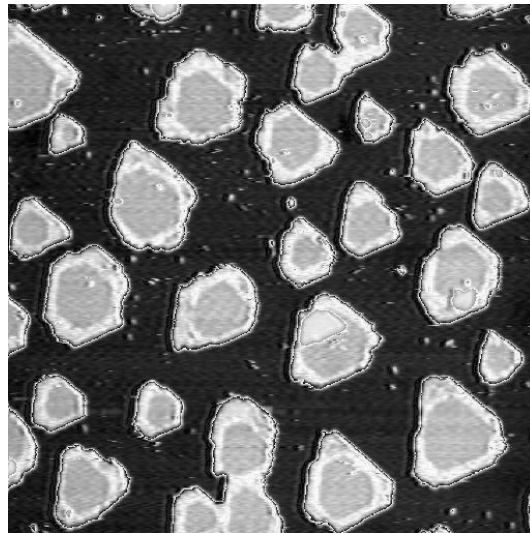
Pt
 $T_{\text{dep}} = 200\text{K}$
 $\Theta = 0.2\text{ ML}$



Annealing
to 800 K



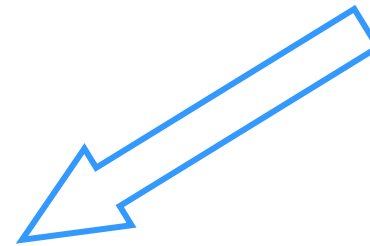
10 nm

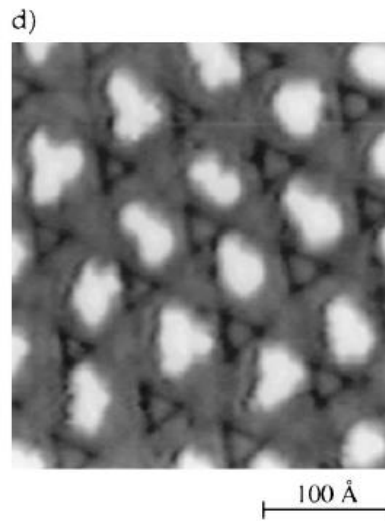
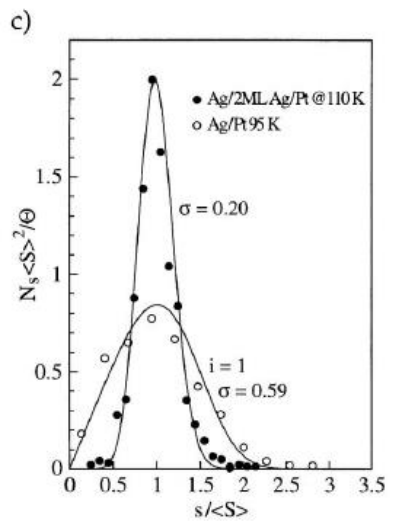
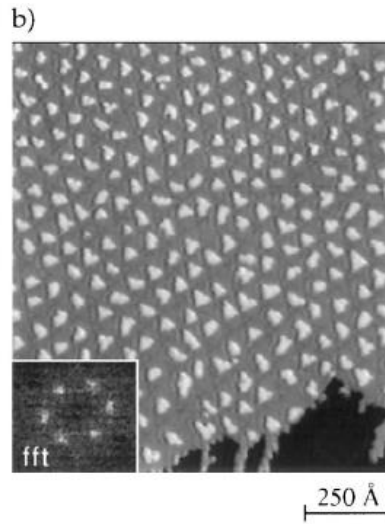
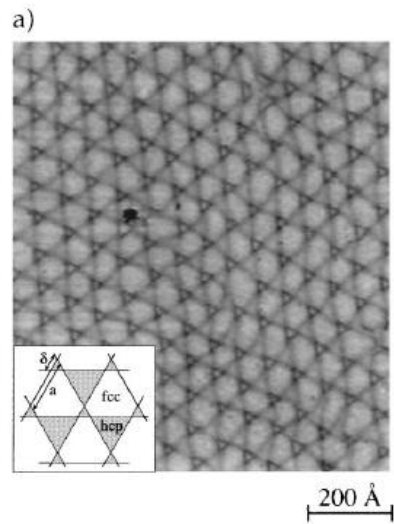


30 nm

$\text{Co}_x\text{Fe}_{1-x}$ decoration

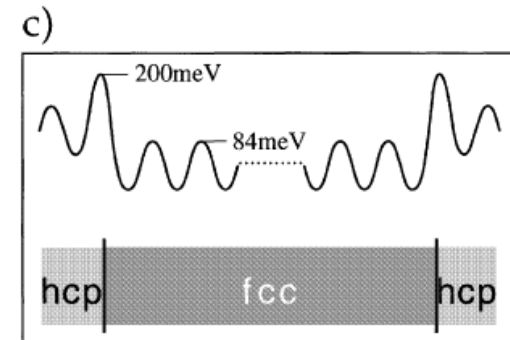
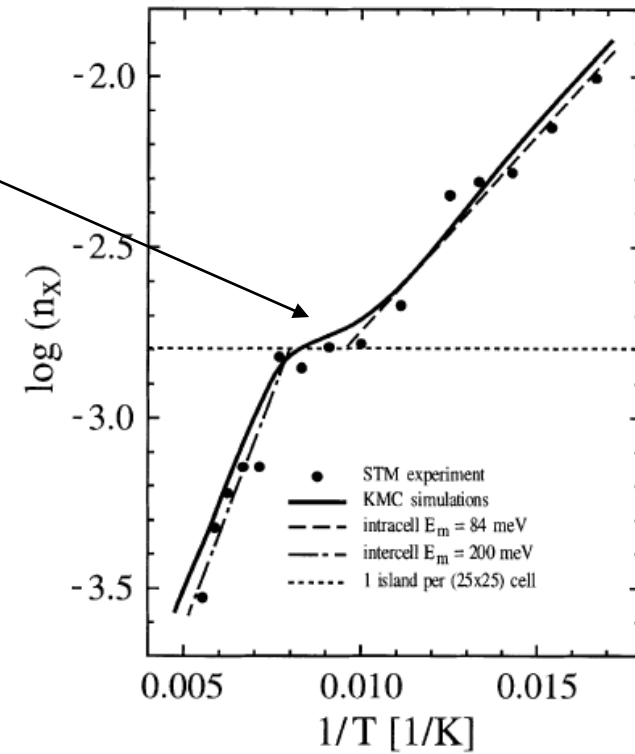
$T_{\text{dep}} = 250\text{K}$
 $\Theta = 0.2\text{ ML}$





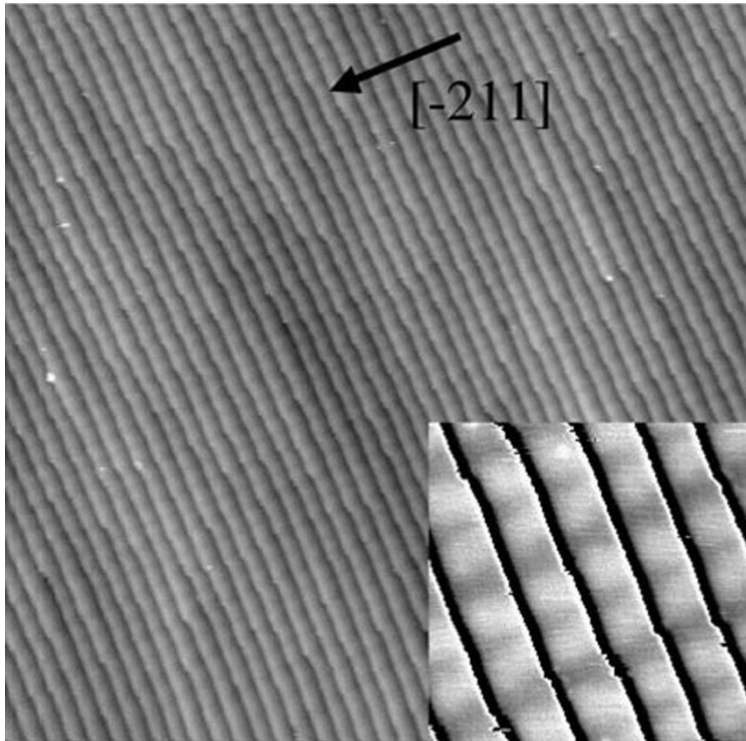
Self-organized growth of nanostructure arrays on strain-relief patterns

Island confinement

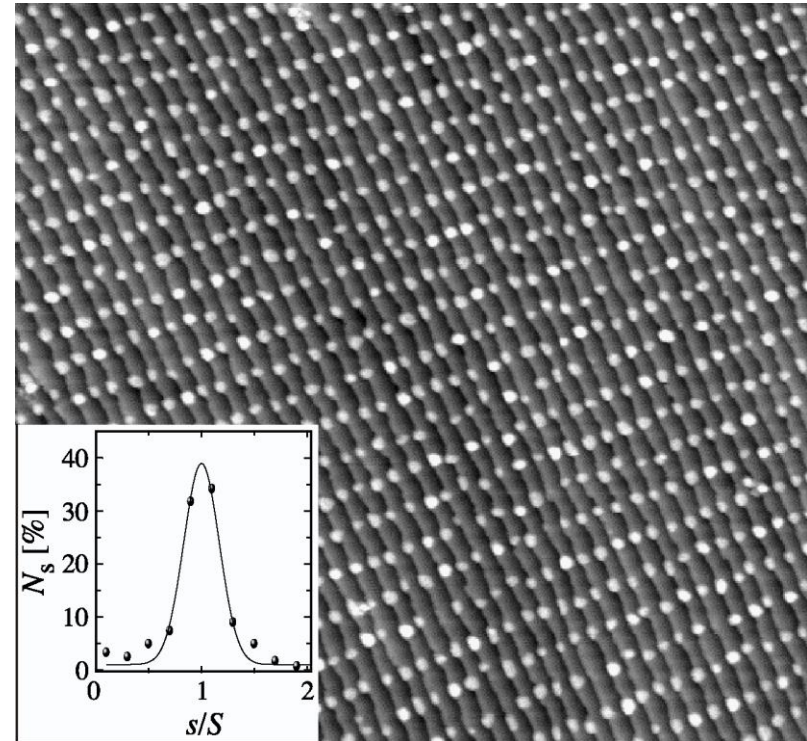


Nucleation of an island superlattice on a reconstruction network. (a) STM image of the domain wall network formed by the second Ag monolayer on Pt(111). (b) Ag nucleation on this network at $T = 110\text{K}$ ($\theta = 0.10\text{ ML}$). (c) **Almost monodispersed size distributions are associated with the periodic island spacing.** (d) Detail showing that islands form exclusively on the fcc stacking areas

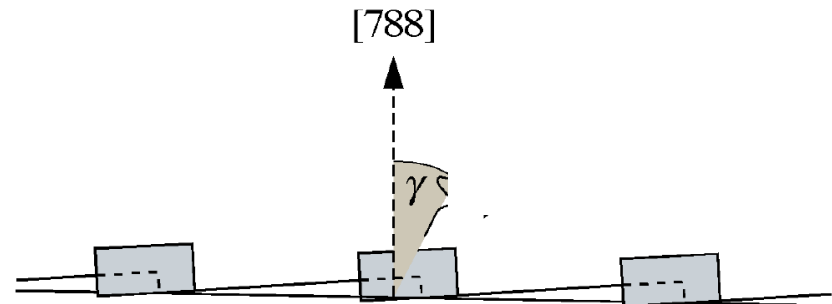
0.2 ML Co $T_{\text{dep}} = 130 \text{ K}$ $T_{\text{ann}} = 400 \text{ K}$



30 nm

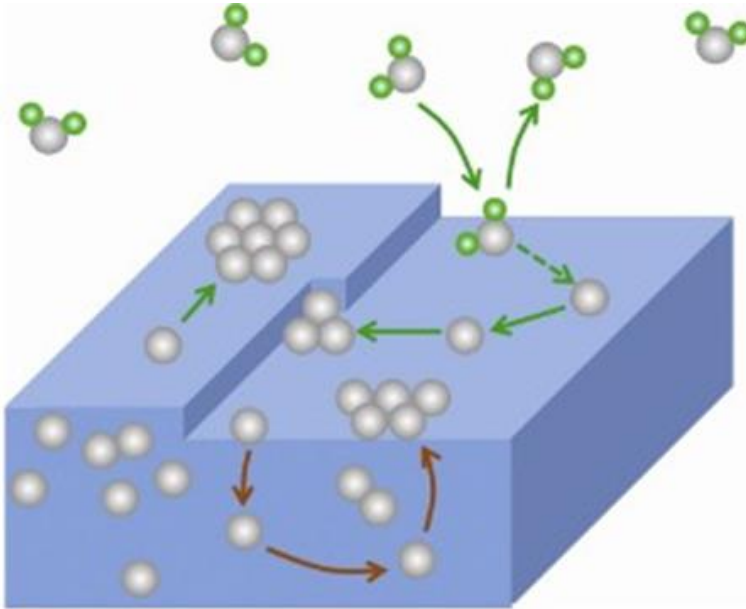


30 nm



Graphene growth

hydrocarbons flux



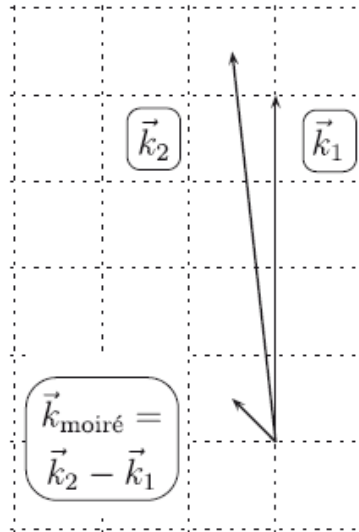
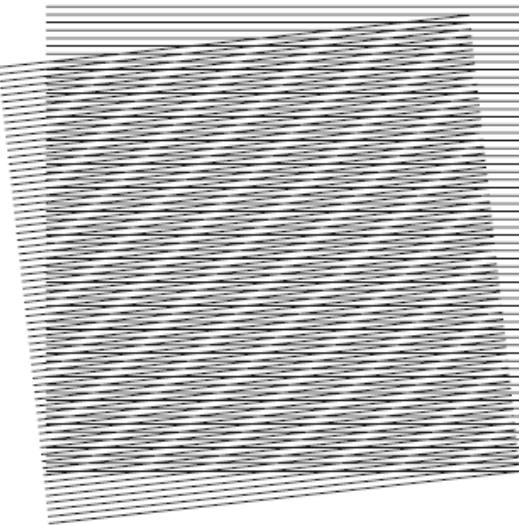
Hydrocarbons molecules brakes on the hot surface: H atoms leave the surface while C atoms organize in the honeycomb network of graphene

- Hydrogen
- Carbon

C atoms dissolved in the bulk segregate to the sample surface and form graphene

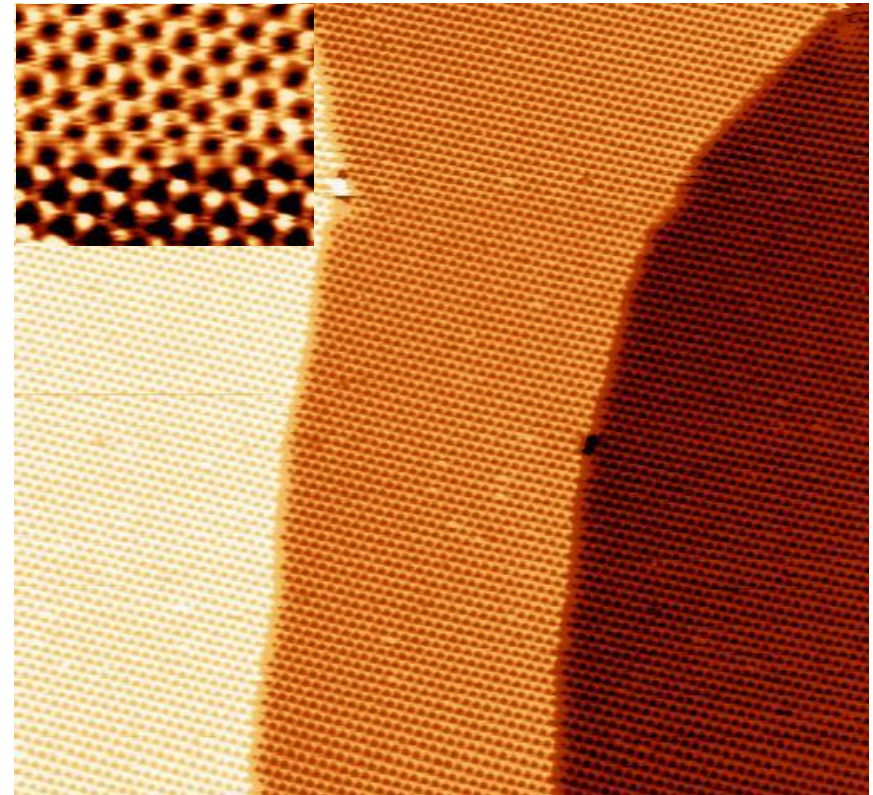
Self-organized growth of nanostructure arrays on moiré patterns: Graphene/Ir(111)

A moiré is a superposition of two lattices generating a third one.



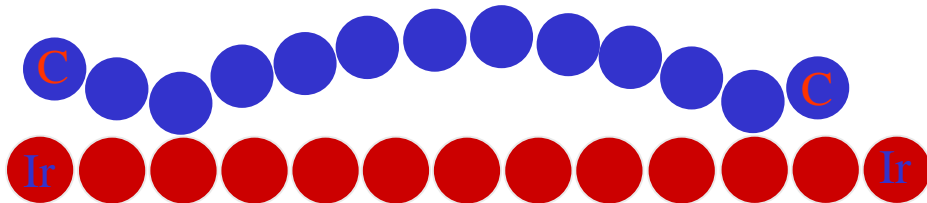
$$a_{\text{Ir}} = 0.27 \text{ nm}$$

$$a_{\text{C}} = 0.245 \text{ nm}$$



180 x 200 nm²

Supercell with (10x10) C atoms
on (9x9) Ir substrate atoms



Self-organized growth of nanostructure arrays on moiré patterns: Graphene/Ir(111)

Graphene/Ir(111)+Ir

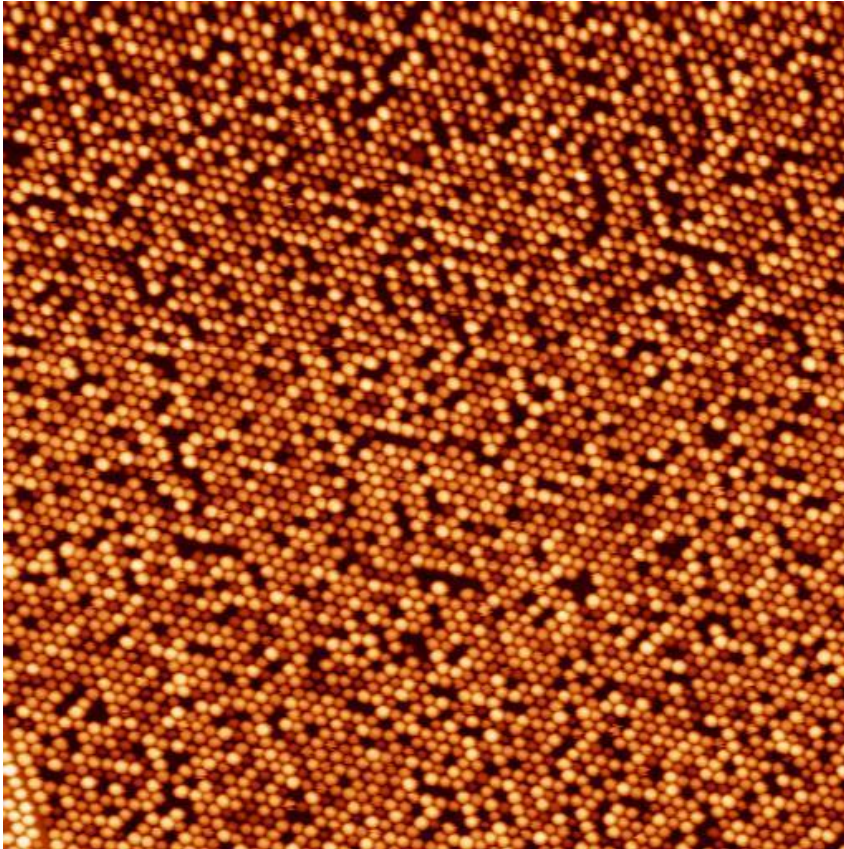
Ir deposition:

I=10.5 A, V=4.90 volts T=375 K

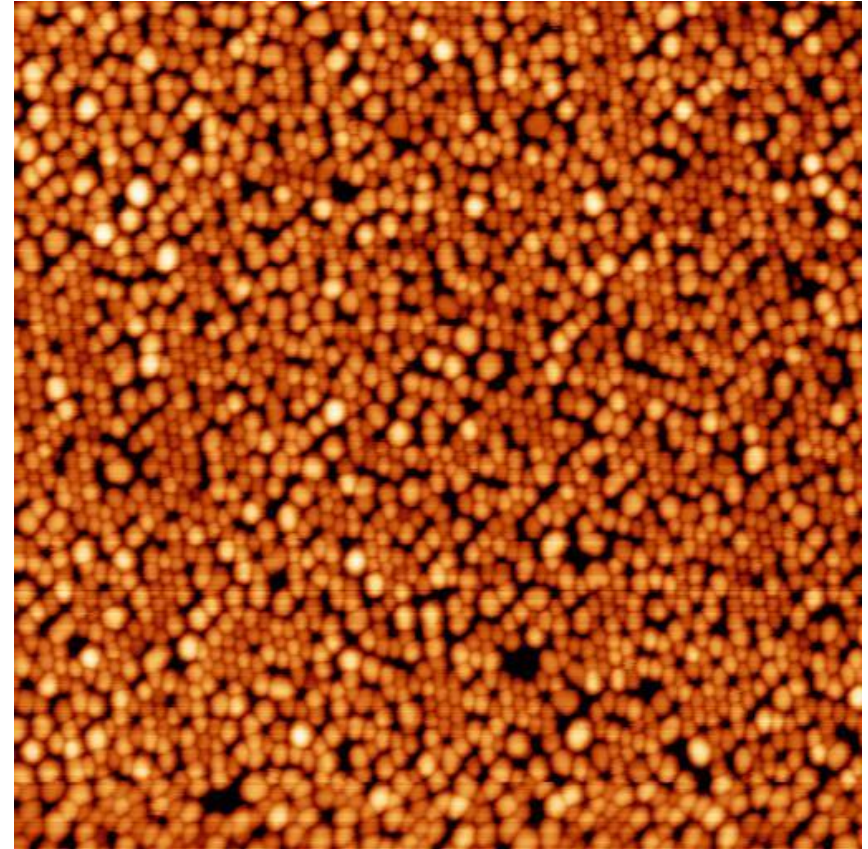
Graphene/Ir(111)+Ir+Co

Ir dep.: I=10.5 A, V=4.90 volts T=375 K

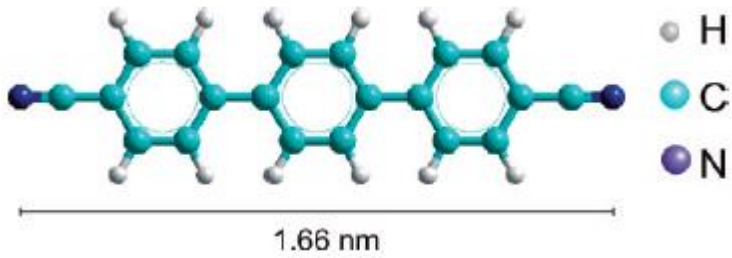
Co dep.: 1 ML tdep=8 min T=300 K



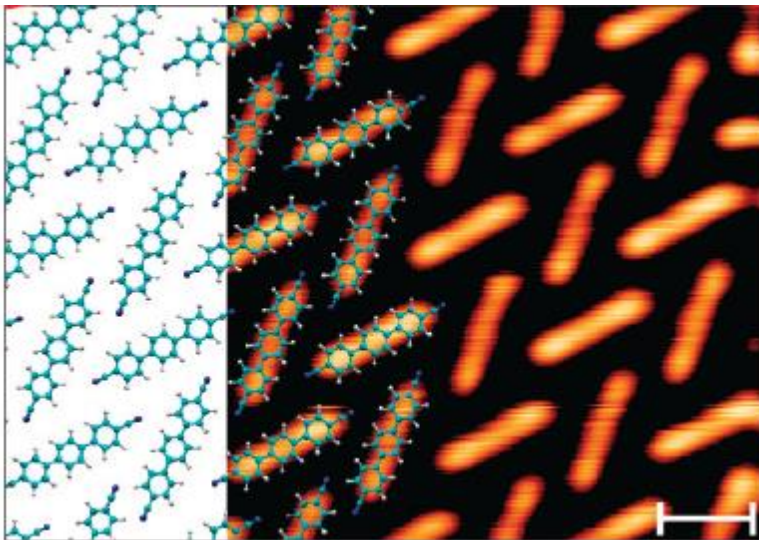
150 x 150 nm²



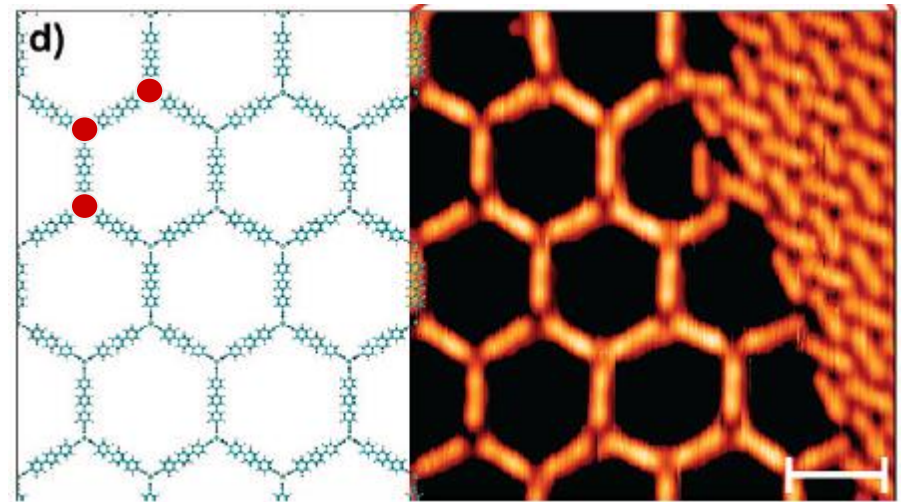
150 x 150 nm²



On Ag(111)

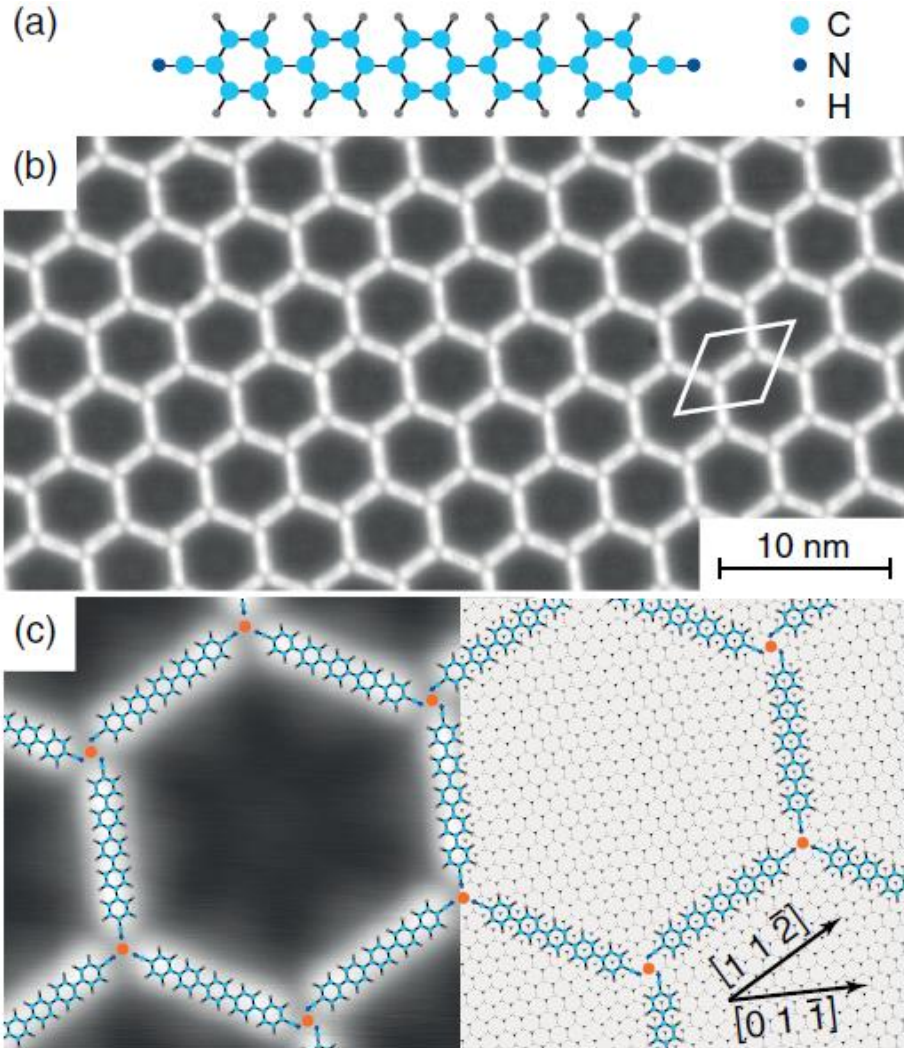


● Cobalt

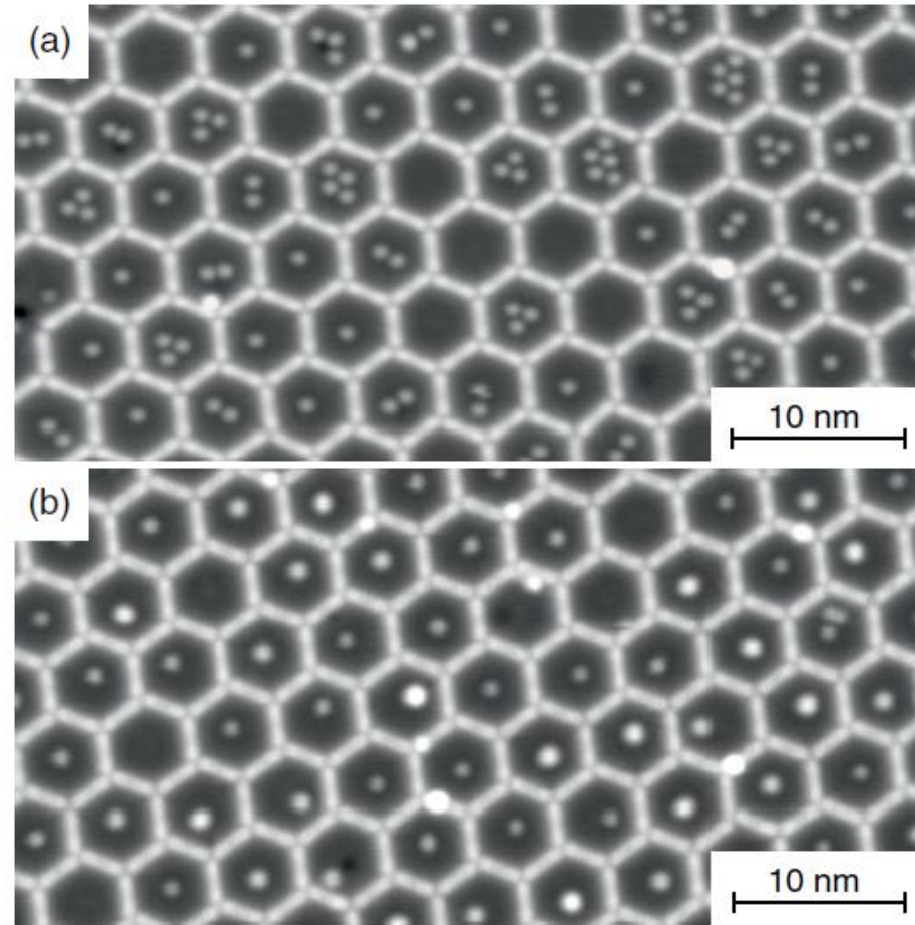


Co atoms added at room temperature
coordinate the molecules in a 3-fold
coordinated motif

Metal organic quantum box network



Metal organic quantum box network a) after Fe deposition



Metal organic quantum box network b) after Fe deposition and annealing to $T_{\text{ann}} = 18\text{K}$

System	density	T_b
Co/Au(11,12,12)	$15 T_{\text{dot}}/\text{in}^2$	75 K
Fe/Co/Au(11,12,12)	$15 T_{\text{dot}}/\text{in}^2$	105 K
Co/Au(788)	$26 T_{\text{dot}}/\text{in}^2$	50 K
Co/GdAu ₂ /Au(111)	$52 T_{\text{dot}}/\text{in}^2$	< 90 K
Fe/NC-Ph ₃ -CN/Cu(111)	$90 T_{\text{dot}}/\text{in}^2$?
Fe/Al ₂ O ₃ /Ni ₃ Al(111)	$92 T_{\text{dot}}/\text{in}^2$?
Co/Ir/graphene/Ir(111)	$116 T_{\text{dot}}/\text{in}^2$	< 50 K